P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)		
- 20	0.0029 at V _{GS} = - 10 V	- 110	120 nC		
- 20	0.0033 at V _{GS} = - 4.5 V	- 90	120110		

Bottom View

DFN5X6

- PIN1

Top View

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested

APPLICATIONS

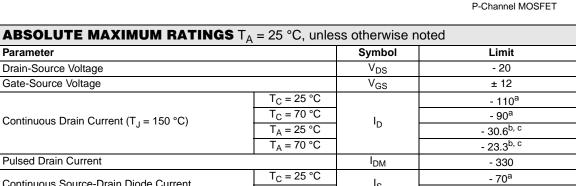
Notebook

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- Load Switch



Top View

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Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 20	V
Gate-Source Voltage		V _{GS}	± 12	v
	T _C = 25 °C		- 110 ^a	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	- 90 ^a	
	T _A = 25 °C	U	- 30.6 ^{b, c}	
	T _A = 70 °C		- 23.3 ^{b, c}	А
Pulsed Drain Current		I _{DM}	- 330	~
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 70 ^a	
Continuous Source-Drain Diode Current	T _A = 25 °C	'8	- 56 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 60	
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	250	mJ
	T _C = 25 °C		170	
Maximum Power Dissipation	T _C = 70 °C	P _D	83	w
	T _A = 25 °C	' D	7.95 ^{b, c}	~~
	T _A = 70 °C		5.0 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	15	20	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	0.9	1.2	0/10

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed

copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 54 °C/W.



Unit





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GO



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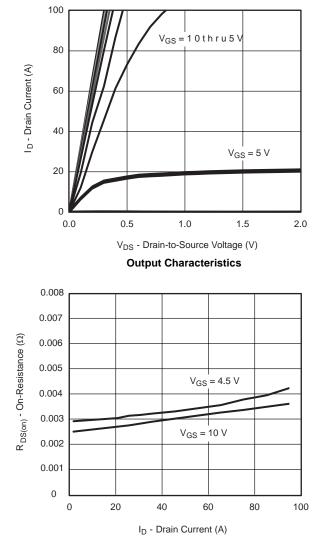
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	ll = - 250 μA		- 31		m\//01	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	i _D = - 250 μA		6.5		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.3		- 1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
Zana Cata Maltana Drain Current	1	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$			- 10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 350			А	
		V _{GS} = - 10 V, I _D = - 20 A		0.0029	0.0032	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 15 A		0.0033	0.0037		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 20 A		93		S	
Dynamic ^b							
Input Capacitance	C _{iss}			12220			
Output Capacitance	C _{oss}	V_{DS} = - 15 V, V_{GS} = 0 V, f = 1 MHz		1931		pF	
Reverse Transfer Capacitance	C _{rss}			976			
Total Gate Charge	Qg	V_{DS} = - 15 V, V_{GS} = - 10 V, I_{D} = - 20 A		230	340		
				78	140	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_{D} = - 20 A		29			
Gate-Drain Charge	Q _{gd}			37			
Gate Resistance	Rg	f = 1 MHz		2.9		Ω	
Turn-On Delay Time	t _{d(on)}			25	30		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		15	30	1	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 10 V, R_g = 1 Ω		110	170		
Fall Time	t _f			30	50		
Turn-On Delay Time	t _{d(on)}			110	170	ns	
Rise Time	t _r	V_{DD} = - 15 V, R _L = 15 Ω		100	150		
Turn-Off Delay Time	t _{d(off)}	$\rm I_D \cong$ - 1.0 A, $\rm V_{GEN}$ = - 4.5 V, $\rm R_g$ = 1 Ω		100	150		
Fall Time	t _f			50	75		
Drain-Source Body Diode Characteristic	cs				•		
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			110	٨	
Pulse Diode Forward Current ^a	I _{SM}				370	A	
Body Diode Voltage	V _{SD}	I _S = - 5 A		- 0.54	- 1.1	V	
Body Diode Reverse Recovery Time	t _{rr}			50	100	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 3.5 A, dl/dt = 100 A/μs, T _{.1} = 25 °C		65	130	nC	
Reverse Recovery Fall Time	t _a	$r_{\rm F} = 5.5$ A, unut = 100 A/µs, $r_{\rm J} = 25$ °C		26			
Reverse Recovery Rise Time	t _b	-1 1		24		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

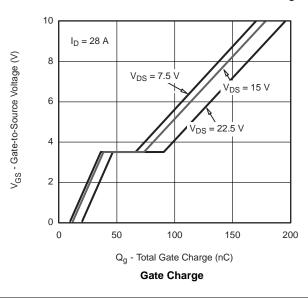
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

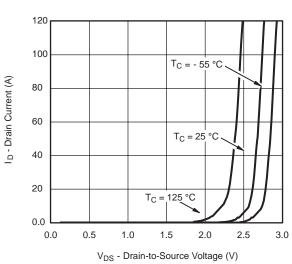




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

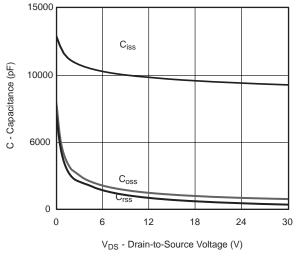




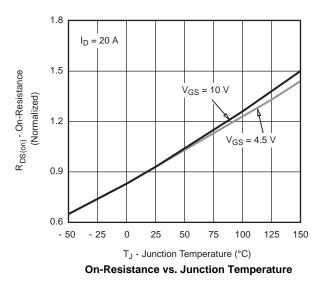


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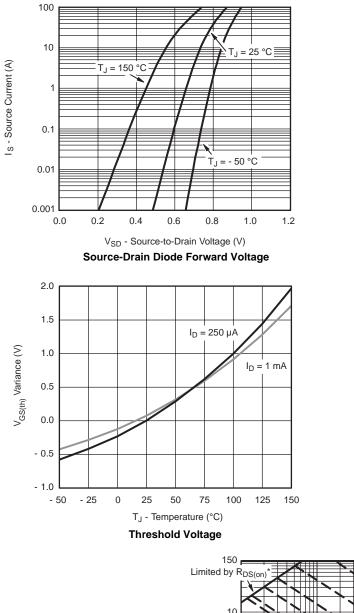
Transfer Characteristics



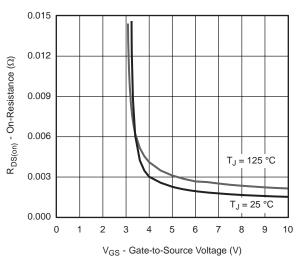
Capacitance



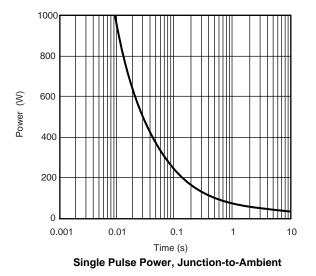


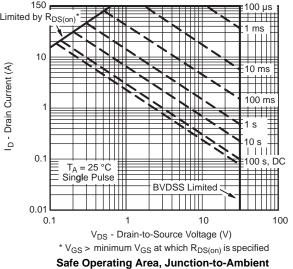


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Gate-to-Source Voltage

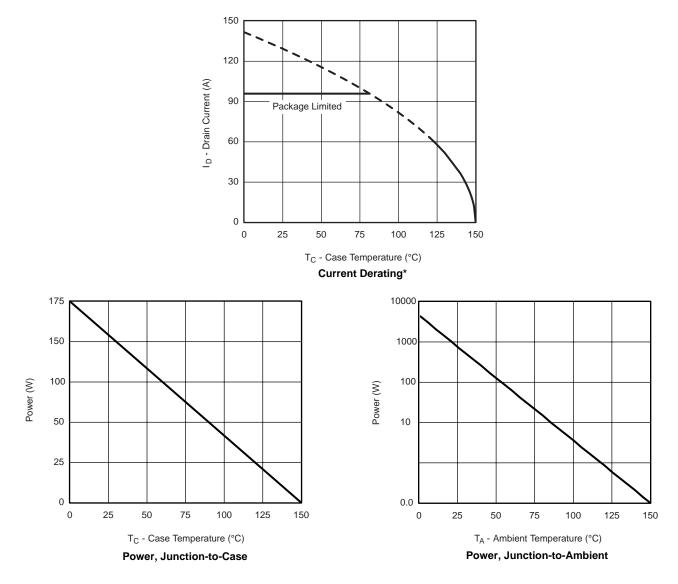






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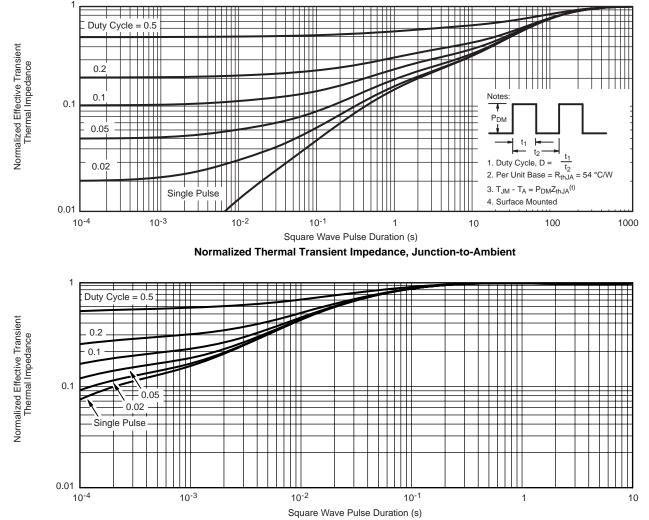


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

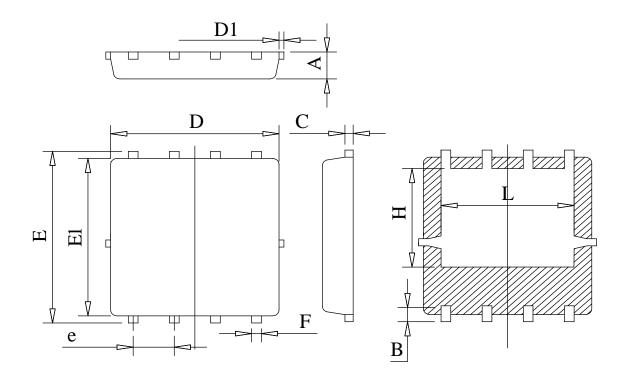


Normalized Thermal Transient Impedance, Junction-to-Case



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DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit : mm			
Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25



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